

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A III group nitride system compound semiconductor light emitting element, comprising:

a transparent substrate that comprises a material other than a III group nitride system compound semiconductor;

a convex light trapping member that is formed over a surface of the transparent substrate; and

a III group nitride system compound semiconductor layer that is formed on the surface of the transparent substrate;

wherein the light trapping member has a refractive index substantially equal to a refractive index of the transparent substrate or closer to the refractive index of the transparent substrate than a refractive index of the III group nitride system compound semiconductor layer, and

wherein an interface is provided between the light trapping member and the transparent substrate.

2. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein the transparent substrate comprises sapphire, and

wherein the light trapping member comprises at least one of Al_2O_3 , Eu_2O_3 , La_2O_3 , Sm_2O_3 , WO_3 and Y_2O_3 .

3-5. (Canceled)

6. (Currently Amended) A pretreated transparent substrate, comprising:

a transparent substrate that comprises a material other than a III group nitride system compound semiconductor; and

a convex light trapping member that is formed over a surface of the transparent

substrate;

wherein the light trapping member has a refractive index substantially equal to a refractive index of the transparent substrate or closer to the refractive index of the transparent substrate than a refractive index of a III group nitride system compound semiconductor, and

wherein an interface is provided between the light trapping member and the transparent substrate.

7. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member is formed directly on the surface of the transparent substrate.

8. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, further comprising:

a buffer layer disposed on the surface of said transparent substrate,

wherein said convex light trapping member is formed on the buffer layer such that the buffer layer is disposed between said convex light trapping member and said transparent substrate.

9. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member comprises an uneven pattern formed across the surface of the substrate, from a first end of the substrate to a second end of the substrate.

10. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 8, wherein said buffer layer comprises at least one of AlN, GaN, InN, AlGaN, InGaN and AlInGaN.

11. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member

comprises:

inclined side portions; and
a top portion positioned between said inclined side portions.

12. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein a light component projecting onto a top surface of the convex light trapping member at an incident angle of more than approximately 47 degrees is subjected to total reflection, and

wherein other light components are trapped into the convex light trapping member and the transparent substrate and are discharged outside of the transparent substrate.

13. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein light entering into said convex light trapping member is directly transmitted through said transparent substrate and then discharged outside of said substrate.

14. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member is formed independently from said transparent substrate.

15. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member comprises a width of $0.1\mu\text{m}$ to $10\mu\text{m}$, a pitch of $0.2\mu\text{m}$ to $20\mu\text{m}$ and a height of $0.1\mu\text{m}$ to $5\mu\text{m}$.

16. (Previously Presented) The pretreated transparent substrate according to claim 6, wherein the transparent substrate comprises sapphire, and

wherein the light trapping member comprises at least one of Al_2O_3 , Eu_2O_3 , La_2O_3 , Sm_2O_3 , WO_3 and Y_2O_3 .

17. (Previously Presented) The pretreated transparent substrate according to claim 6, wherein said convex light trapping member is formed directly on the surface of the transparent substrate.

18. (Previously Presented) The pretreated transparent substrate according to claim 6, further comprising:

a buffer layer disposed on the surface of said transparent substrate,
wherein said convex light trapping member is formed on the buffer layer such that the buffer layer is disposed between said convex light trapping member and said transparent substrate.

19. (Previously Presented) The pretreated transparent substrate according to claim 6, wherein said convex light trapping member comprises an uneven pattern formed across the surface of the substrate, from a first end of the substrate to a second end of the substrate.

20. (Previously Presented) The pretreated transparent substrate according to claim 6, wherein said convex light trapping member comprises:

inclined side portions; and
a top portion positioned between said inclined side portions.

21. (Previously Presented) The pretreated transparent substrate according to claim 6, wherein a light component projecting onto a top surface of the convex light trapping member at an incident angle of more than approximately 47 degrees is subjected to total reflection, and

wherein other light components are trapped into the convex light trapping member and the transparent substrate and are discharged outside of the transparent substrate.

22. (Currently Amended) A light emitting diode, comprising:

a III group nitride system compound semiconductor light emitting element,

comprising:

a transparent substrate that comprises a material other than a III group nitride system compound semiconductor;

a convex light trapping member that is formed over a surface of the transparent substrate; and

a III group nitride system compound semiconductor layer that is formed on the surface of the transparent substrate,

wherein the light trapping member has a refractive index substantially equal to a refractive index of the transparent substrate or closer to the refractive index of the transparent substrate than a refractive index of the III group nitride system compound semiconductor layer, and

wherein an interface is provided between the light trapping member and the transparent substrate.

23. (Canceled)

24. (Previously Presented) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein light entering into said light emitting member is directly transmitted through the transparent substrate.

25. (Previously Presented) The pretreated transparent substrate according to claim 6, wherein light entering into said light emitting member is directly transmitted through the transparent substrate.

26. (Previously Presented) The light emitting diode according to claim 22, wherein light entering into said light emitting member is directly transmitted through the transparent substrate.